TOSHIBA

Unit in mm

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155311

HIGH VOLTAGE, HIGH SPEED SWITCHING APPLICATIONS.

• Low Forward Voltage : V_F=0.94V (Typ.)

• High Voltage : V_R=400V (Min.)

• Fast Reverse Recovery Time : t_{rr}=1.5μs (Typ.)

• Small Total Capacitance : C_T=3.2pF (Typ.)

• Small Package : SC-59

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	v_{RM}	420	V	
Reverse Voltage	$V_{\mathbf{R}}$	400	V	
Maximum (Peak) Forward Current	I _{FM} 300		mA	
Average Forward Current	IO	100	mA	
Surge Current (10ms)	I_{FSM}	2	Α	
Power Dissipation	P	150	mW	
Junction Temperature	$T_{ m j}$	125	°C	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C	

1. ANODE 2. N.C. S-MINI 3. CATHODE

TOSHIBA 1-3G1B Weight: 0.012g

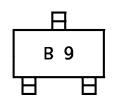
SC-59

EIAJ

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

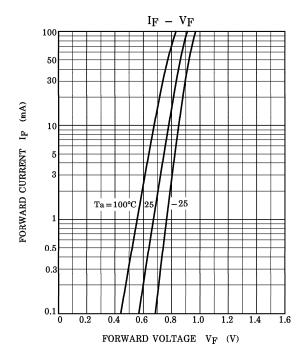
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$v_{F(1)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.80	_	V
	$V_{F(2)}$	$I_{\mathbf{F}} = 100 \text{mA}$		0.94	1.20	
Reverse Current	$I_{R(1)}$	$V_R = 300V$	_	_	0.1	μ A
	$I_{R(2)}$	$V_R = 400V$	_	_	1.0	
Total Capacitance	$\mathbf{C_{T}}$	$V_R=0$, f=1MHz	_	3.2	5.0	pF
Reverse Recovery Time	${ m t_{rr}}$	$I_{ m F}$ = 10mA	_	1.5	_	μ s

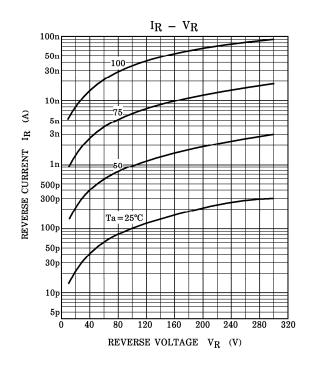
MARKING

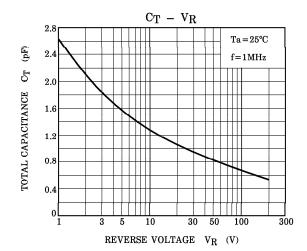


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